

60V 3A N-Channel Enhancement Mode Power MOSFET

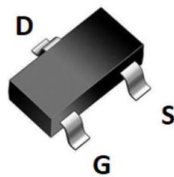
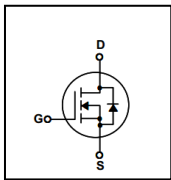
General Description

This Power MOSFET has been developed using advanced trench process, which is specifically designed to minimize input capacitance and gate charge. This renders the device suitable for use as primary switch in advanced high-efficiency isolated DC-DC converters for telecom and computer applications, and applications with low gate charge driving requirements.

FEATURES

- $R_{DS(ON)} \leq 100m\Omega$ @ $V_{GS}=10V, I_D=3A$
- Excellent $R_{DS(ON)}$ and Low Gate Charge
- Lead free product is acquired

SYMBOL



SOT-23 top view

ASSEMBLY MESSAGE

Product Name	Package	Packaging
BXT1000N06M	SOT-23	Reel

ABSOLUTE MAXIMUM RATINGS ($T_C=25^\circ\text{C}$ unless otherwise noted)

Parameter		Symbol	Rating	Unit
			SOT-23	
Drain-Source Voltage		V_{DSS}	60	V
Drain Current	Continuous ($T_C = 25^\circ\text{C}$)	I_D	3	A
	Continuous ($T_C = 100^\circ\text{C}$)		2	A
Drain Current	Pulsed (Note1)	I_{DM}	12	A
Gate-Source Voltage		V_{GSS}	± 20	V
Power Dissipation	$T_C = 25^\circ\text{C}$	P_D	1.5	W
Maximum Junction Temperature		T_J	150	$^\circ\text{C}$
Storage Temperature Range		T_{STG}	-55 to 150	$^\circ\text{C}$

Note: 1. Repetitive Rating: Pulse width limited by maximum junction temperature

